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Product: Ultrafast Recovery Rectifiers

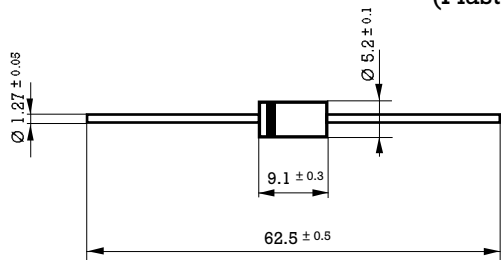

FAGOR ELECTRONICA's Ultrafast Recovery Rectifiers offer reverse recovery times down to 30ns using broad range of forward current possibilities and packages.

Ideal for high frequency applications like SMPS, Monitors, Electronic Ballast, Inverters....

Manufactured using HYPERECTIFIER© technology, we offer these devices housed either in leaded packages or SMD.

Product	Family	$I_{F(AV)}$ (A)	I_{FSM} (A)	V_{RRM} (V)	V_F (V)	T_{RR} (ns)	OUTLINE
EGP50B	EGP50	5.0	150	100	1.0	50	DO201-AD

5 Amp. Glass Passivated Avalanche Ultrafast Recovery Rectifier

<p>Dimensions in mm.</p> <p style="text-align: right;">DO-201AD (Plastic)</p>  <p>Mounting instructions</p> <ol style="list-style-type: none"> 1. Min. distance from body to soldering point, 4 mm. 2. Max. solder temperature, 350 °C. 3. Max. soldering time, 3.5 sec. 4. Do not bend lead at a point closer than 3 mm. to the body. 	<p style="text-align: center;">Voltage 50 to 400 V.</p> <p style="text-align: center;">Current 5 A at 55 °C.</p> <div style="text-align: center; margin: 10px 0;">  </div> <ul style="list-style-type: none"> • Glass Passivated Junction • High current capability • The plastic material carries U/L recognition 94 V-0 • Terminals: Axial Leads • Polarity: Color band denotes cathode
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Maximum Ratings, according to IEC publication No. 134

		EGP50A	EGP50B	EGP50D	EGP50F	EGP50G
V_{RRM}	Peak Recurrent reverse voltage (V)	50	100	200	300	400
V_{RMS}	Maximum RMS voltage	35	70	140	210	280
V_{DC}	Maximum DC blocking voltage	50	100	200	300	400
$I_{F(AV)}$	Forward current at $T_{amb} = 55\text{ °C}$	5 A				
I_{FRM}	Recurrent peak forward current (A)	50 A				
I_{FSM}	8.3 ms. peak forward surge current <small>(Jedec Method)</small>	150 A				
t_{tr}	Max. reverse recovery time from $I_F = 0.5\text{ A}$; $I_R = 1\text{ A}$; $I_{RR} = 0.25\text{ A}$	50 ns				
C_j	Typical Junction Capacitance at 1 MHz and reverse voltage of $4V_{DC}$	100 pF				
T_j	Operating temperature range	- 65 to + 150 °C				
T_{stg}	Storage temperature range	- 65 to + 150 °C				
E_{RSM}	Maximum non repetitive peak reverse avalanche energy. $I_R = 1\text{ A}$; $T_J = 25\text{ °C}$	20 mJ				

Electrical Characteristics at $T_{amb} = 25\text{ °C}$

V_F	Max. forward voltage drop at $I_F = 5\text{ A}$	1.0V	1.25 V
I_R	Max. reverse current at V_{RRM} at 25 °C at 150 °C	5 $\mu\text{ A}$ 50 $\mu\text{ A}$	
R_{thj-a}	Max. thermal resistance (l = 10 mm.)	20 °C/W	